

December 2008

FOD814 Series, FOD617 Series, FOD817 Series 4-Pin High Operating Temperature Phototransistor Optocouplers

Description

The FOD814 consists of two gallium arsenide infrared emitting diodes, connected in inverse parallel, driving a

silicon phototransistor output in a 4-pin dual in-line

package. The FOD617/817 Series consists of a gallium

arsenide infrared emitting diode driving a silicon

phototransistor in a 4-pin dual in-line package.

Features

- AC input response (FOD814 only)
- Applicable to Pb-free IR reflow soldering
- Compact 4-pin package

Current transfer ratio in selected groups: FOD617A: 40–80% FOD617B: 63–125% FOD817A: 80–160% FOD617C: 100–200% FOD817B: 130–260% FOD617D: 160–320% FOD817C: 200–400% FOD814: 20–300% FOD817D: 300–600% FOD814A: 50–150%

- C-UL, UL and VDE approved
- High input-output isolation voltage of 5000Vrms
- Minimum BV_{CEO} of 70V guaranteed
- Higher operating temperatures (versus H11AXXX counterparts)

Applications

FOD814 Series

- AC line monitor
- Unknown polarity DC sensor
- Telephone line interface
- FOD617 and FOD817 Series

Power supply regulators Digital logic inputs Microprocessor inputs

FOD814 FOD817/817

Absolute Maximum Ratings (T_A = 25°C Unless otherwise specified.)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

		Va	lue	Units
Symbol	Parameter	FOD814	FOD617/817	
TOTAL DEVIC	E			
T _{STG}	Storage Temperature	-55 to	o +150	°C
T _{OPR}	Operating Temperature	-55 to +105	-55 to +110	°C
T _{SOL}	Lead Solder Temperature	260 fo	r 10 sec	°C
P _{TOT}	Total Power Dissipation	2	00	mW
EMITTER				
I _F	Continuous Forward Current	±50	50	mA
V _R	Reverse Voltage		6	
PD	Power Dissipation		70	mW
	Derate above 100°C	1	.7	mW/°C
DETECTOR				
V _{CEO}	Collector-Emitter Voltage	-	70	V
V _{ECO}	Emitter-Collector Voltage	6	6 (FOD817)	V
			7 (FOD617)	
Ι _C	Continuous Collector Current	Į	50	mA
P _C	Collector Power Dissipation	1	50	mW
	Derate above 90°C	2	2.9	mW/°C

FOD814 Series, FOD617 Series, FOD817 Series -
Series, FOD817 Series —
- 4-Pin High Operatin
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Electrical Characteristics ($T_A = 25^{\circ}C$ Unless otherwise specified.)
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Individual Component Characteristics

Symbol	Parameter	Device	Test Conditions	Min.	Тур.*	Max.	Unit
EMITTER					1	1	
V _F	Forward Voltage	FOD814	$I_F = \pm 20 \text{mA}$		1.2	1.4	V
		FOD617	I _F = 60mA		1.35	1.65	
		FOD817	I _F = 20mA		1.2	1.4	
I _R	Reverse Leakage Current	FOD617	V _R = 6.0V		0.001	10	μA
		FOD817	V _R = 4.0V			10	
Ct	Terminal Capacitance	FOD814	V = 0, f = 1 kHz		50	250	pF
		FOD617	V = 0, f = 1kHz		30	250	
		FOD817	V = 0, f = 1kHz		30	250	
DETECTOR	2						
I _{CEO}	Collector Dark Current	FOD814	$V_{CE} = 20V, I_F = 0$			100	nA
		FOD617C/D	$V_{CE} = 10V, I_F = 0$		1	100	
		FOD617A/B	$V_{CE} = 10V, I_F = 0$		1	50	
		FOD817	$V_{CE} = 20V, I_F = 0$			100	
BV _{CEO}	Collector-Emitter Breakdown	FOD814	$I_{\rm C} = 0.1 {\rm mA}, I_{\rm F} = 0$	70			V
	Voltage	FOD617	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm F} = 0$	70			

FOD817

FOD814

FOD617

FOD817

 $I_{\rm C} = 0.1 {\rm mA}, I_{\rm F} = 0$

 $I_{E} = 10 \mu A, I_{F} = 0$

 $I_{E} = 10 \mu A, I_{F} = 0$

 $I_{E} = 10 \mu A, I_{F} = 0$

70

6

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Transfer Characteristics

Voltage

Emitter-Collector Breakdown

 BV_{ECO}

Symbol	DC Characteristic	Device	Test Conditions	Min.	Typ.*	Max.	Unit
CTR	Current Transfer	FOD814	$I_{F} = \pm 1 \text{mA}, V_{CE} = 5V^{(1)}$	20		300	%
	Ratio	FOD814A		50		150	
		FOD617A	$I_F = 10mA, V_{CE} = 5V^{(1)}$	40		80	
		FOD617B		63		125	
		FOD617C		100		200	
		FOD617D		160		320	
		FOD617A	$I_F = 1 \text{mA}, V_{CE} = 5 V^{(1)}$	13		1	
		FOD617B		22			
		FOD617C		34			
		FOD617D		56			
		FOD817	$I_F = 5mA, V_{CE} = 5V^{(1)}$	50		600	
		FOD817A		80		160	
		FOD817B		130		260	
		FOD817C		200		400	
		FOD817D		300		600	
V _{CE (sat)}	Collector-Emitter	FOD814	$I_F = \pm 20$ mA, $I_C = 1$ mA		0.1	0.2	V
. ,	Saturation Voltage	FOD617	$I_{\rm F} = 10 {\rm mA}, I_{\rm C} = 2.5 {\rm mA}$			0.4	
		FOD817	$I_{\rm F} = 20 {\rm mA}, I_{\rm C} = 1 {\rm mA}$		0.1	0.2	1

Electrical Characteristics (T_A = 25°C Unless otherwise specified.) (Continued)

Transfer Characteristics (Continued)

Symbol	AC Characteristic	Device	Test Conditions	Min.	Тур.*	Max.	Unit
f _C	Cut-Off Frequency	FOD814	V_{CE} = 5V, I_C = 2mA, R_L = 100 Ω , -3dB	15	80		kHz
t _r	Response Time (Rise)	FOD814	$V_{CE} = 2 \text{ V}, \text{ I}_{C} = 2\text{mA}, \text{ R}_{L} = 100\Omega^{(2)}$		4	18	μs
		FOD617					
		FOD817					
t _f	Response Time (Fall)	FOD814			3	18	μs
		FOD617					
		FOD817					

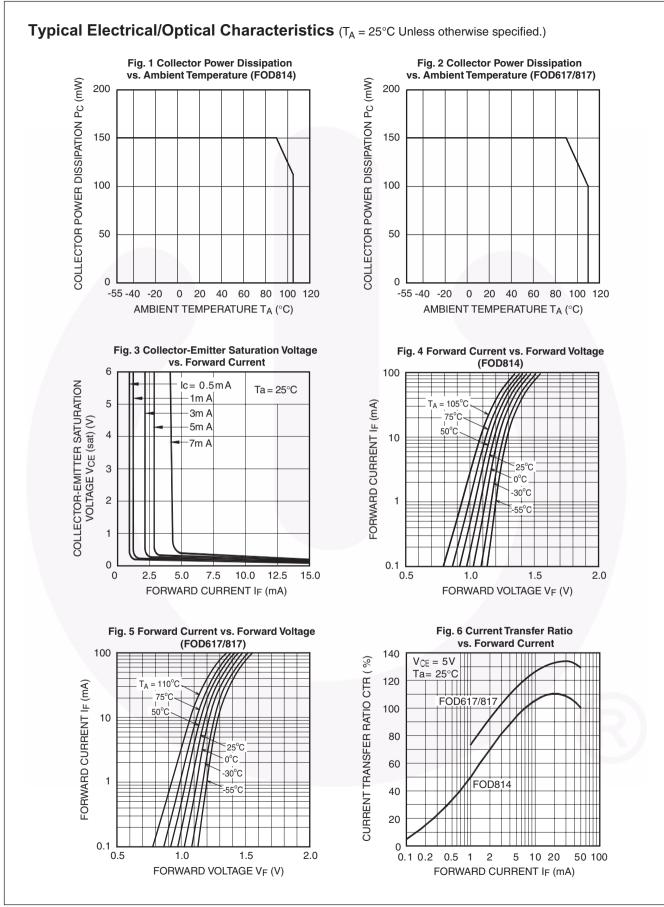
Isolation Characteristics

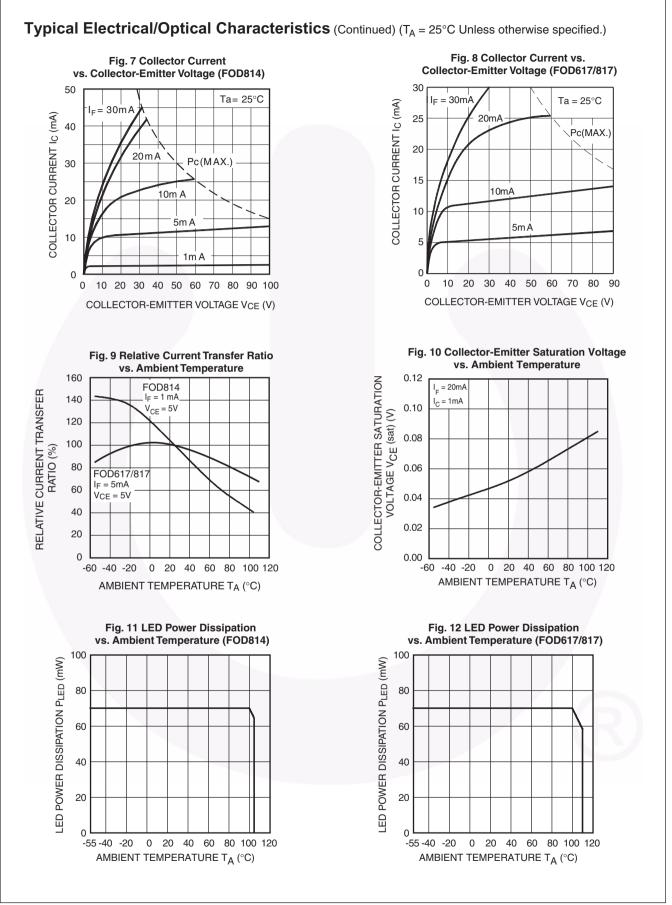
Symbol	Characteristic	Device	Test Conditions	Min.	Тур.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage ⁽³⁾	FOD814	f = 60Hz, t = 1 min,	5000			Vac(rms)
	Voltage ⁽³⁾	FOD617	I _{I-O} ≤ 2μA				
		FOD817					
R _{ISO}	Isolation Resistance	FOD814	V _{I-O} = 500VDC	5x10 ¹⁰	1x10 ¹¹		Ω
		FOD617					
		FOD817					
C _{ISO}	Isolation Capacitance	FOD814	$V_{I-O} = 0, f = 1 MHz$		0.6	1.0	pf
		FOD617]				
		FOD817]				

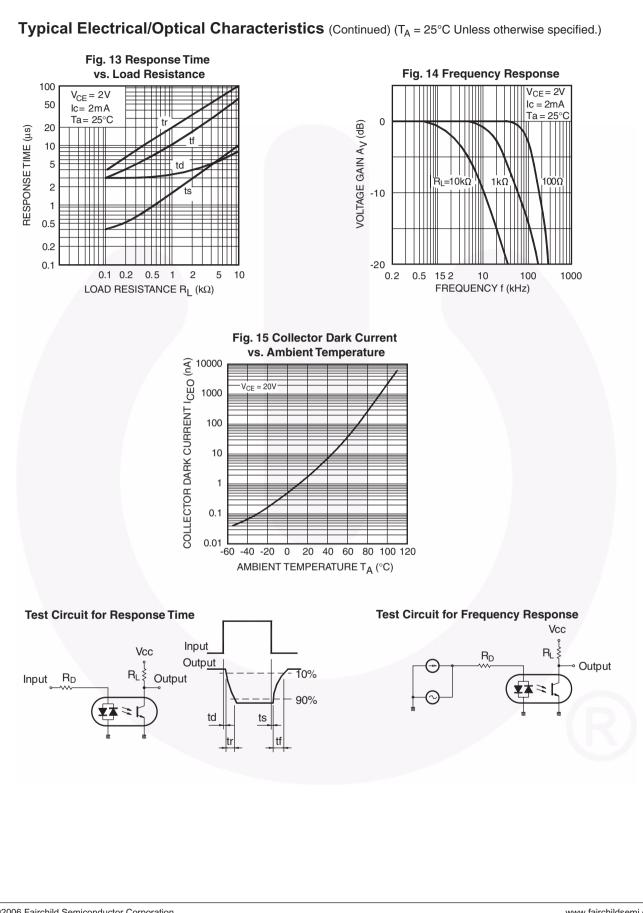
*Typical values at T_A = 25°C

Notes:

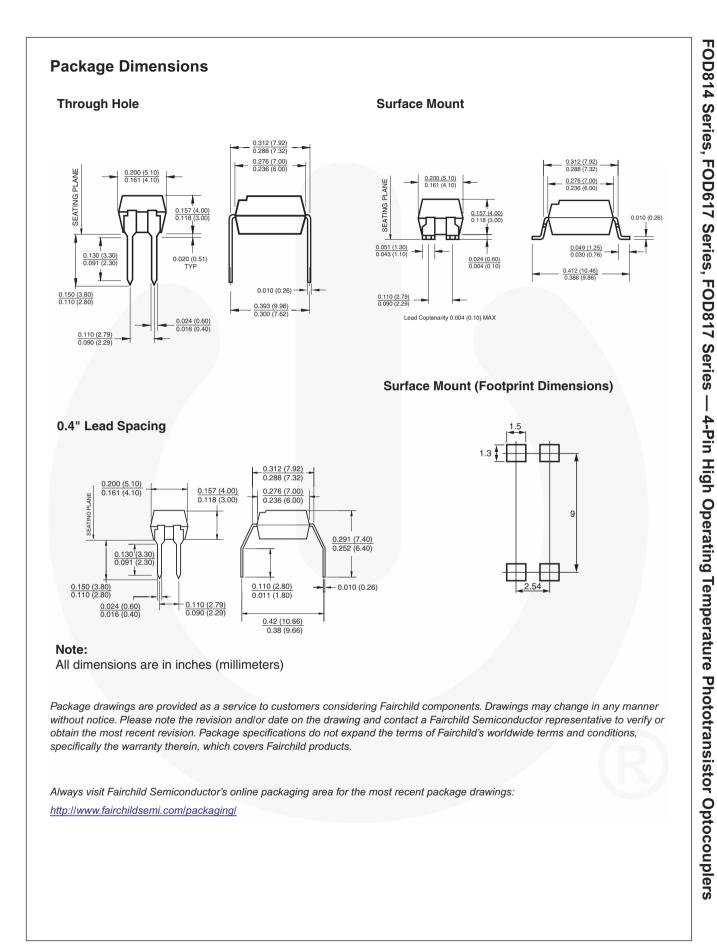
- 1. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
- 2. For test circuit setup and waveforms, refer to page 4.
- 3. For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.





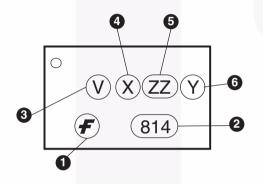


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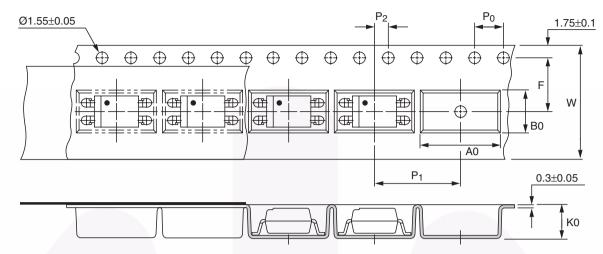
rdering Information			
Option	Part Number Example	Description	
S	FOD814S	Surface Mount Lead Bend	
SD	FOD814SD	Surface Mount; Tape and reel	
W	FOD814W	0.4" Lead Spacing	
300	FOD814300	VDE Approved	
300W	FOD814300W	VDE Approved, 0.4" Lead Spacing	
3S	FOD8143S	VDE Approved, Surface Mount	
3SD	FOD8143SD	VDE Approved, Surface Mount, Tape & Reel	

Marking Information



Definiti	Definitions		
1	Fairchild logo		
2	Device number		
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)		
4	One digit year code		
5	Two digit work week ranging from '01' to '53'		
6	Assembly package code		

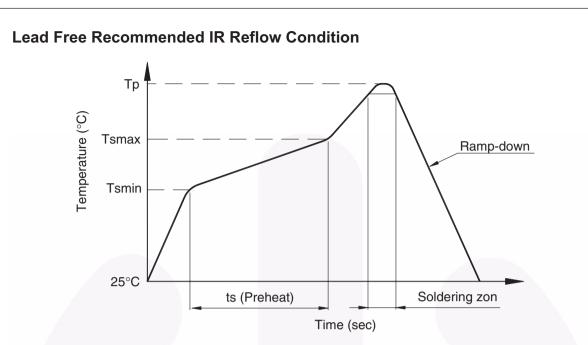
Carrier Tape Specifications



Note:

All dimensions are in millimeters.

Symbol	Description	Dimensions in mm (inches)
W	Tape wide	16 ± 0.3 (.63)
P ₀	Pitch of sprocket holes	4 ± 0.1 (.15)
F P ₂	Distance of compartment	7.5 ± 0.1 (.295) 2 ± 0.1 (.079)
P ₁	Distance of compartment to compartment	12 ± 0.1 (.472)
A0	Compartment	10.45 ± 0.1 (.411)
B0		5.30 ± 0.1 (.209)
K0		4.25 ± 0.1 (.167)



Profile Feature	Pb-Sn solder assembly	Lead Free assembly
Preheat condition (Tsmin-Tsmax / ts)	100°C ~ 150°C 60 ~ 120 sec	150°C ~ 200°C 60 ~120 sec
Melt soldering zone	183°C 60 ~ 120 sec	217°C 30 ~ 90 sec
Peak temperature (Tp)	240 +0/-5°C	260 +0/-5°C
Ramp-down rate	6°C/sec max.	6°C/sec max.

Recommended Wave Soldering condition

Profile Feature	For all solder assembly
Peak temperature (Tp)	Max 260°C for 10 sec



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Rev. 137